

ABSTRACT

HIGH-PURITY COPPER-MANGANESE-ALLOY SPUTTERING TARGET

5 Provided is a high-purity copper-manganese-alloy sputtering target comprising 0.05 to 20 wt% of Mn and the remainder being Cu and inevitable impurities. The high-purity copper-manganese-alloy sputtering target is characterized in that the in-plane variation (CV value) in Mn concentration of the target is 3% or less. It is thus possible to form a thin film having excellent uniformity by adding an appropriate amount of a Mn element to copper and reducing the in-plane variation of the sputtering target. In particular, there is
10 provided a high-purity copper-manganese-alloy sputtering target which is useful for improving the yield and the reliability of semiconductor products which are making progress in a degree of refinement and integration.